



## Automotive N-Channel 100 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY                                    |        |
|--|--------|
| V <sub>DS</sub> (V)                                | 100    |
| R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V  | 0.0089 |
| R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 4.5 V | 0.0112 |
| I <sub>D</sub> (A)                                 | 50     |
| Configuration                                      | Single |

### FEATURES

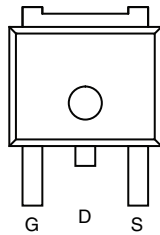
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

AUTOMOTIVE GRADE



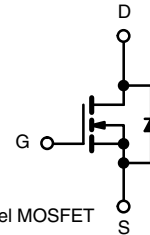
RoHS COMPLIANT HALOGEN FREE

TO-252



Top View

Drain Connected to Tab



N-Channel MOSFET

| ORDERING INFORMATION            |                   |
|---------------------------------|-------------------|
| Package                         | TO-252            |
| Lead (Pb)-free and Halogen-free | SQD50N10-8m9L-GE3 |

| ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                                     |                                   |               |      |
|---|-------------------------------------|-----------------------------------|---------------|------|
| PARAMETER   |                                     | SYMBOL                            | LIMIT         | UNIT |
| Drain-Source Voltage  |                                     | V <sub>DS</sub>                   | 100           | V    |
| Gate-Source Voltage   |                                     | V <sub>GS</sub>                   | ± 20          |      |
| Continuous Drain Current  | T <sub>C</sub> = 25 °C <sup>a</sup> | I <sub>D</sub>                    | 50            | A    |
|   | T <sub>C</sub> = 125 °C             |                                   | 49            |      |
| Continuous Source Current (Diode Conduction) <sup>a</sup>                 |                                     | I <sub>S</sub>                    | 50            |      |
| Pulsed Drain Current <sup>b</sup>   |                                     | I <sub>DM</sub>                   | 200           |      |
| Single Pulse Avalanche Current  | L = 0.1 mH                          | I <sub>AS</sub>                   | 43            |      |
| Single Pulse Avalanche Energy   |                                     | E <sub>AS</sub>                   | 92            |      |
| Maximum Power Dissipation <sup>b</sup>                                    | T <sub>C</sub> = 25 °C              | P <sub>D</sub>                    | 136           | W    |
|   | T <sub>C</sub> = 125 °C             |                                   | 45            |      |
| Operating Junction and Storage Temperature Range                          |                                     | T <sub>J</sub> , T <sub>stg</sub> | - 55 to + 175 | °C   |

| THERMAL RESISTANCE RATINGS |                        |                   |       |      |
|----------------------------|------------------------|-------------------|-------|------|
| PARAMETER                  |                        | SYMBOL            | LIMIT | UNIT |
| Junction-to-Ambient        | PCB Mount <sup>c</sup> | R <sub>thJA</sub> | 50    | °C/W |
| Junction-to-Case (Drain)   |                        | R <sub>thJC</sub> | 1.1   |      |

### Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).



| SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted) |              |   |   |      |        |           |               |
|---|--------------|---|---|------|--------|-----------|---------------|
| PARAMETER   | SYMBOL       | TEST CONDITIONS   |   | MIN. | TYP.   | MAX.      | UNIT          |
| <b>Static</b>   |              |   |   |      |        |           |               |
| Drain-Source Breakdown Voltage  | $V_{DS}$     | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$  |   | 100  | -      | -         | V             |
| Gate-Source Threshold Voltage   | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$  |   | 1.5  | 2.0    | 2.5       |               |
| Gate-Source Leakage   | $I_{GSS}$    | $V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$  |   | -    | -      | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current   | $I_{DSS}$    | $V_{GS} = 0\text{ V}$   | $V_{DS} = 100\text{ V}$                                     | -    | -      | 1         | $\mu\text{A}$ |
|   |              | $V_{GS} = 0\text{ V}$   | $V_{DS} = 100\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$ | -    | -      | 50        |               |
|   |              | $V_{GS} = 0\text{ V}$   | $V_{DS} = 100\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$ | -    | -      | 500       |               |
| On-State Drain Current <sup>a</sup>   | $I_{D(on)}$  | $V_{GS} = 10\text{ V}$  | $V_{DS} \geq 5\text{ V}$                                    | 50   | -      | -         | A             |
| Drain-Source On-State Resistance <sup>a</sup>                               | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$  | $I_D = 15\text{ A}$   | -    | 0.0071 | 0.0089    | $\Omega$      |
|   |              | $V_{GS} = 10\text{ V}$  | $I_D = 15\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$     | -    | -      | 0.0151    |               |
|   |              | $V_{GS} = 10\text{ V}$  | $I_D = 15\text{ A}$ , $T_J = 175\text{ }^\circ\text{C}$     | -    | -      | 0.0187    |               |
|   |              | $V_{GS} = 4.5\text{ V}$   | $I_D = 10\text{ A}$   | -    | 0.0089 | 0.0112    |               |
| Forward Transconductance <sup>b</sup>                                       | $g_{fs}$     | $V_{DS} = 15\text{ V}$ , $I_D = 15\text{ A}$  |   | -    | 67     | -         | S             |
| <b>Dynamic<sup>b</sup></b>  |              |   |   |      |        |           |               |
| Input Capacitance   | $C_{iss}$    | $V_{GS} = 0\text{ V}$   | $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$                 | -    | 2340   | 2950      | $\text{pF}$   |
| Output Capacitance  | $C_{oss}$    |   |   | -    | 1441   | 1810      |               |
| Reverse Transfer Capacitance  | $C_{rss}$    |   |   | -    | 124    | 160       |               |
| Total Gate Charge <sup>c</sup>  | $Q_g$        | $V_{GS} = 10\text{ V}$  | $V_{DS} = 50\text{ V}$ , $I_D = 50\text{ A}$                | -    | 46     | 70        | nC            |
| Gate-Source Charge <sup>c</sup>   | $Q_{gs}$     |   |   | -    | 7.5    | -         |               |
| Gate-Drain Charge <sup>c</sup>  | $Q_{gd}$     |   |   | -    | 10     | -         |               |
| Gate Resistance   | $R_g$        | f = 1 MHz   |   | 6    | 12.3   | 18.5      | $\Omega$      |
| Turn-On Delay Time <sup>c</sup>   | $t_{d(on)}$  | $V_{DD} = 50\text{ V}$ , $R_L = 1\text{ }\Omega$<br>$I_D \cong 50\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\text{ }\Omega$ |   | -    | 12     | 18        | ns            |
| Rise Time <sup>c</sup>  | $t_r$        |   |   | -    | 12     | 18        |               |
| Turn-Off Delay Time <sup>c</sup>  | $t_{d(off)}$ |   |   | -    | 95     | 145       |               |
| Fall Time <sup>c</sup>  | $t_f$        |   |   | -    | 120    | 180       |               |
| <b>Source-Drain Diode Ratings and Characteristics<sup>b</sup></b>           |              |   |   |      |        |           |               |
| Pulsed Current <sup>a</sup>   | $I_{SM}$     |   |   | -    | -      | 200       | A             |
| Forward Voltage   | $V_{SD}$     | $I_F = 15\text{ A}$ , $V_{GS} = 0\text{ V}$   |   | -    | 0.8    | 1.5       | V             |

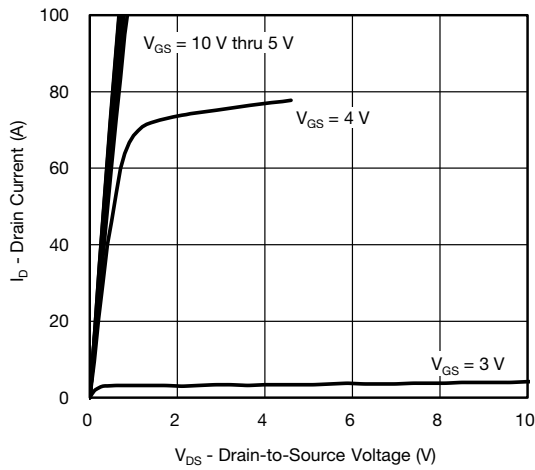
**Notes**

- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

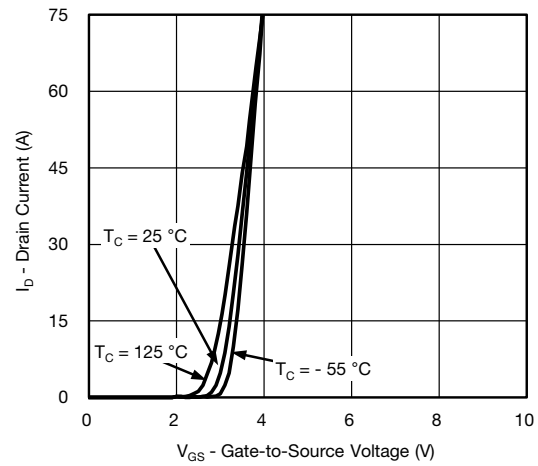
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



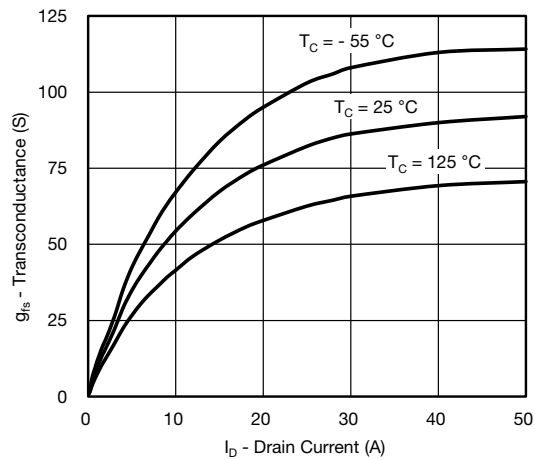
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



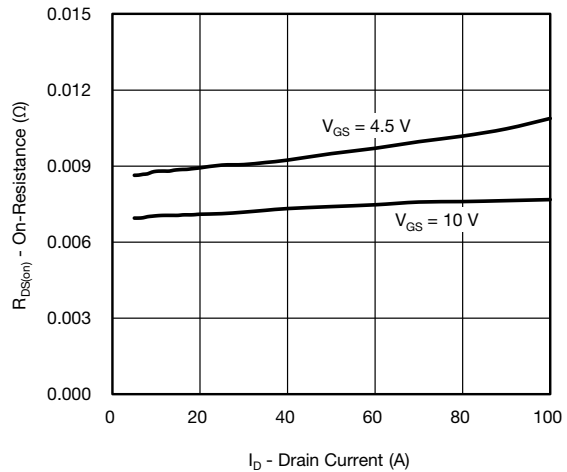
Output Characteristics



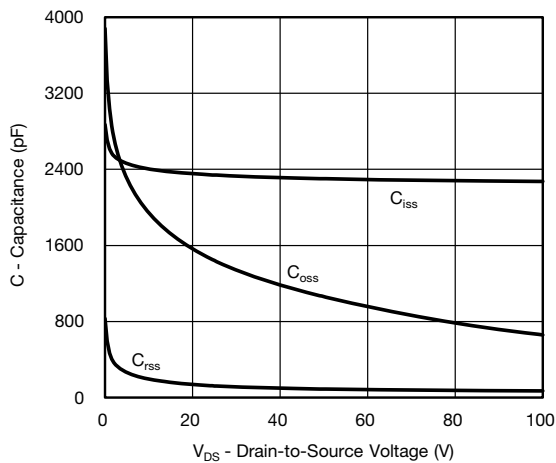
Transfer Characteristics



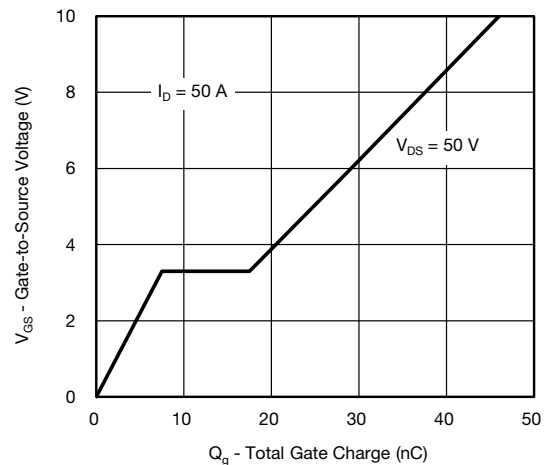
Transconductance



On-Resistance vs. Drain Current



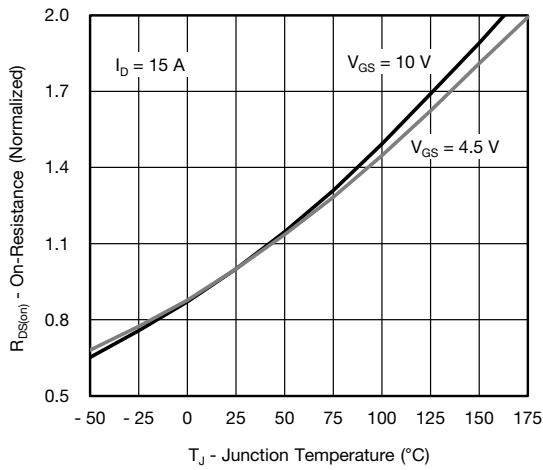
Capacitance



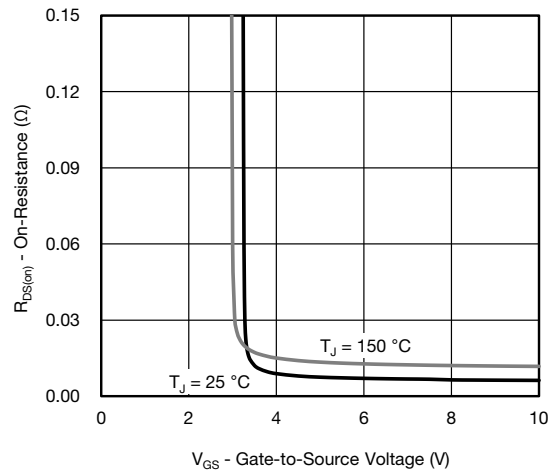
Gate Charge



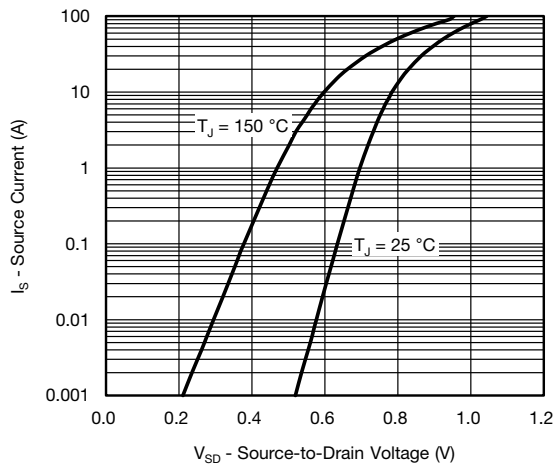
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



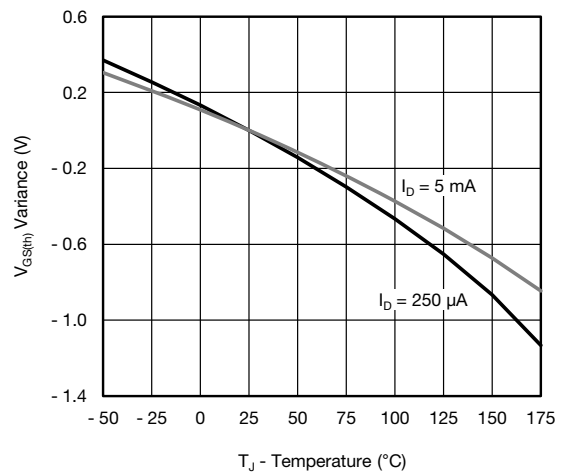
**On-Resistance vs. Junction Temperature**



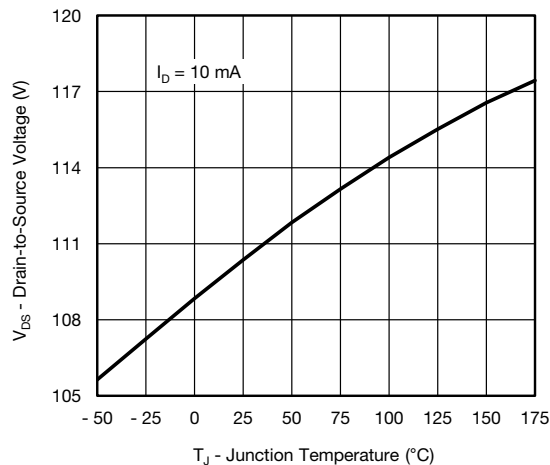
**On-Resistance vs. Gate-to-Source Voltage**



**Source Drain Diode Forward Voltage**



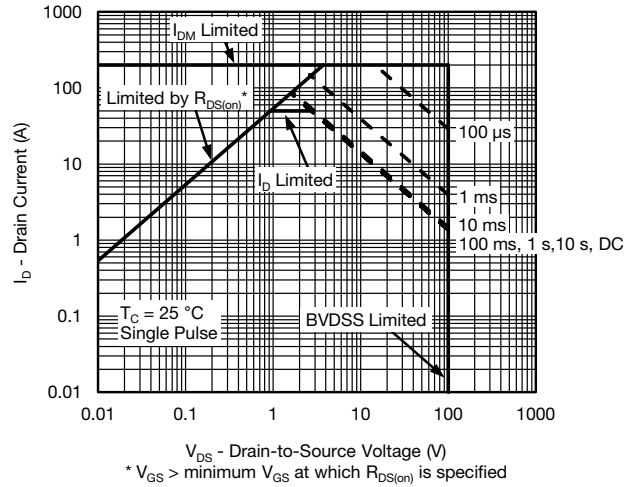
**Threshold Voltage**



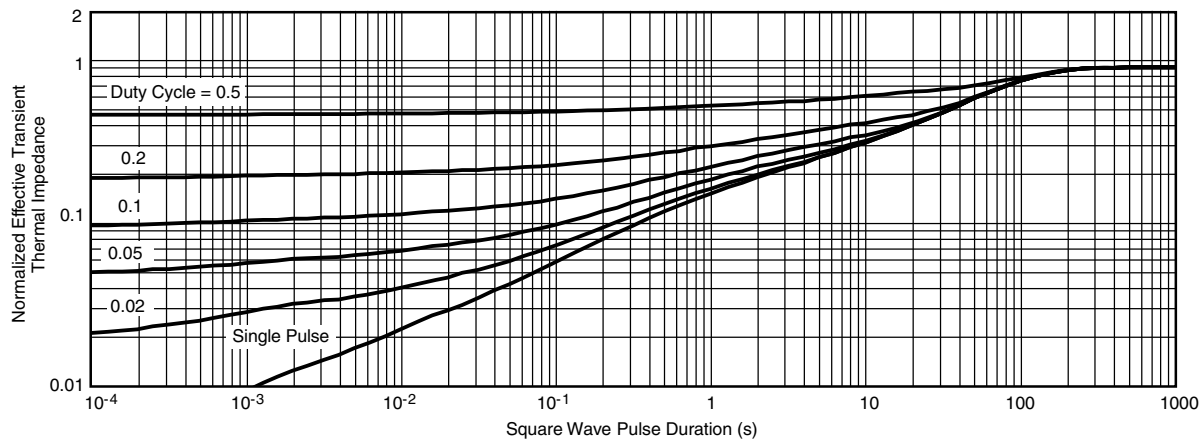
**Drain Source Breakdown vs. Junction Temperature**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



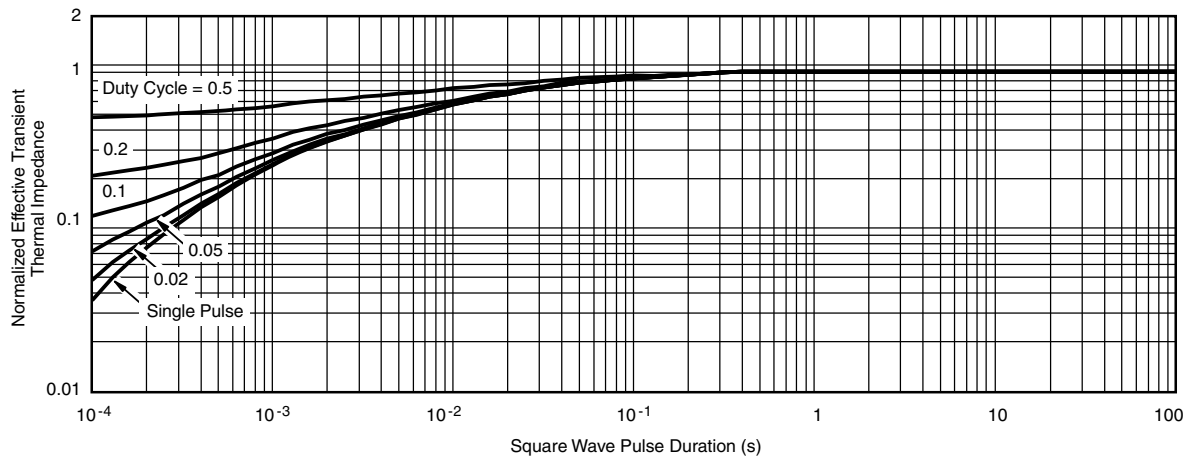
**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?62778](http://www.vishay.com/ppg?62778).



DPAK / TO-252 and Reverse DPAK

Ordering codes for the SQ rugged series power MOSFETs in the DPAK / TO-252 and Reverse DPAK packages:

Table with 3 columns: DATASHEET PART NUMBER, OLD ORDERING CODE a, NEW ORDERING CODE. Lists various MOSFET part numbers and their corresponding ordering codes.

Note

a. Old ordering code is obsolete and no longer valid for new orders



### TO-252AA Case Outline



| DIM.   | MILLIMETERS |       | INCHES    |       |
|--|-------------|-------|-----------|-------|
|  | MIN.        | MAX.  | MIN.      | MAX.  |
| A  | 2.18        | 2.38  | 0.086     | 0.094 |
| A1   | -           | 0.127 | -         | 0.005 |
| b  | 0.64        | 0.88  | 0.025     | 0.035 |
| b2   | 0.76        | 1.14  | 0.030     | 0.045 |
| b3   | 4.95        | 5.46  | 0.195     | 0.215 |
| C  | 0.46        | 0.61  | 0.018     | 0.024 |
| C2   | 0.46        | 0.89  | 0.018     | 0.035 |
| D  | 5.97        | 6.22  | 0.235     | 0.245 |
| D1   | 4.10        | -     | 0.161     | -     |
| E  | 6.35        | 6.73  | 0.250     | 0.265 |
| E1   | 4.32        | -     | 0.170     | -     |
| H  | 9.40        | 10.41 | 0.370     | 0.410 |
| e  | 2.28 BSC    |       | 0.090 BSC |       |
| e1   | 4.56 BSC    |       | 0.180 BSC |       |
| L  | 1.40        | 1.78  | 0.055     | 0.070 |
| L3   | 0.89        | 1.27  | 0.035     | 0.050 |
| L4   | -           | 1.02  | -         | 0.040 |
| L5   | 1.01        | 1.52  | 0.040     | 0.060 |
| ECN: T13-0592-Rev. A, 02-Sep-13<br>DWG: 6019 |             |       |           |       |

**Note**

- Dimension L3 is for reference only.



## RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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